

Table of Contents

Preface

Chapter 1: Bulk and Epitaxial Growth

1.1: Physical Vapor Transport Growth

Advances in <i>In Situ</i> SiC Growth Analysis Using Cone Beam Computed Tomography M. Salamon, M. Arzig, N. Uhlmann and P.J. Wellmann	5
Cold Split Kerf-Free Wafering Results for Doped 4H-SiC Boules M. Swoboda, R. Rieske, C. Beyer, A. Ullrich, G. Gesell and J. Richter	10
Tracking of the Growth Interface during PVT-Growth of SiC Boules Using a X-Ray Computed Tomography Setup M. Arzig, M. Salamon, N. Uhlmann and P.J. Wellmann	14
Modified Hot-Zone Design for Large Diameter 4H-SiC Single Crystal Growth J.W. Choi, J.G. Kim, B.K. Jang, S.K. Ko, M.O. Kyun, J.D. Seo, K.R. Ku, J.M. Choi and W.J. Lee	18
Impacts of TaC Coating on SiC PVT Process Control and Crystal Quality W. Fan, H. Qu, S.I. Chang, B. Kozak, G. Shaffer, A. Galyukov and W.J. Lee	22
Major Carrier Element Concentrations in SiC Powder and Bulk Crystal T.C. Hsiao, S. Tsao, S. Nagalyuk and E. Mokhov	26
Variation of Vanadium Incorporation in Semi-Insulating SiC Single Crystals Grown by PVT Method C.Y. Lee, J.M. Choi, D.S. Kim, M.S. Park, Y.S. Jang, W.J. Lee, I.S. Yang, T.H. Kim, X.F. Chen and X.G. Xu	30
Study on N and B Doping by Closed Sublimation Growth Using Separated Ta Crucible D. Tanaka, H. Kurokawa, S. Kamiyama, T. Takeuchi, M. Iwaya and I. Akasaki	34
Polytype Control by Pretreatment of SiC Source Powder for 4H-SiC Single Crystal Growth J.W. Choi, J.G. Kim, B.K. Jang, S.K. Ko, M.O. Kyun, J.D. Seo, K.R. Ku, C.Y. Lee and W.J. Lee	38
Optimization of the SiC Powder Source Size Distribution for the Sublimation Growth of Long Crystals Boules J. Steiner, M. Arzig, T.C. Hsiao and P.J. Wellmann	42
New Materials for Semi-Insulating SiC Single Crystal Growth by PVT Method J.M. Choi, C.Y. Lee, D.S. Kim, M.S. Park, Y.S. Jang, W.J. Lee, W. Fan, H. Qu, X.F. Chen and X.G. Xu	46
A Comparative Study of the Crystal Growth Techniques of Silicon Carbide, Technology Adaption and the Road to Low Cost Silicon Carbide Materials S.R. Parthasarathy, R. Drachev, B. Bathey and H. Chou	51
Research on the Key Problems in the Industrialization of SiC Substrate Materials P. Gao, J. Xin, C.F. Yan, H.K. Kong, J.J. Chen, X.C. Liu and E.W. Shi	56
Influence of Dopant Concentration on Dislocation Distributions in 150mm 4H SiC Wafers I. Manning, G.Y. Chung, E. Sanchez, M. Dudley, T. Ailihumaer, J.Q. Guo, O. Goue and B. Raghothamachar	60
Study on Dislocation Behaviors during PVT Growth of 4H-SiC I.G. Yeo, T.H. Eun, J.Y. Kim, S.S. Lee, H.S. Seo and M.C. Chun	64

1.2: Solution Growth

Application of Defect Conversion Layer by Solution Growth for Reduction of TSDs in 4H-SiC Bulk Crystals by PVT Growth N. Komatsu, T. Mitani, Y. Hayashi, H. Suo, T. Kato and H. Okumura	71
Effect of Melt-Back Process on the Quality of Grown Crystal in SiC Solution Growth K. Kawaguchi, K. Seki and K. Kusunoki	75

Evaluation of Basal Plane Dislocation Behavior in the Epitaxial Layer on a 4H-SiC Wafer Fabricated by the Solution Growth Method K. Seki, K. Kusunoki, S. Harada and T. Ujihara	80
Solution Growth of 4-Inch Diameter SiC Single Crystal Using Si-Cr Based Solvent K. Kusunoki, Y. Kishida and K. Seki	85

1.3: Epitaxial Growth

High Quality 4H-SiC Epitaxial Layer by Tuning CVD Process N. Piluso, A. Campione, S. Lorenti, A. Severino, G. Arena, S. Coffa and F. La Via	91
Continuous Growth of Buffer/Drift Epitaxial Stack Based on 4H-SiC by Quick Change of N₂ Flow Rate under High Growth Rate Condition Y. Daigo, A. Ishiguro, S. Ishii and T. Kobayashi	97
Repeatability of Epitaxial Growth of n-Type 4H-SiC Films by High Speed Wafer Rotation Vertical CVD Tool Y. Daigo, A. Ishiguro, S. Ishii, Y. Moriyama, K. Suzuki and M. Yajima	101
Extensive 99% Killer Defect Free 4H-SiC Epitaxial Layer toward High Current Large Chip Devices K. Wada, T. Miyase, H. Itoh, T. Hori, H. Doi and M. Furumai	105
Influence of Substrate Properties on the Defectivity and Minority Carrier Lifetime in 4H-SiC Homoepitaxial Layers B. Kallinger, J. Erlekampf, K. Rosshirt, P. Berwian, M. Stockmeier, M. Vogel, P. Hens and F. Wischmeyer	109
Basal Plane Dislocation Conversion Enhancement in 4H-SiC Homo-Epitaxial Layers by Ion Implantation into the Wafer C. Heidorn, R. Esteve, T. Höchbauer, M. Krieger, H.B. Weber and R. Rupp	114
Effect of Surface Etching Conditions on Stacking Faults in 4H-SiC Epitaxy T. Rana, G.Y. Chung, S. Anderson, I. Manning, W. Bowen and E. Sanchez	119
New SiC Epitaxial Growth Process with up to 100% BPD to TED Defect Conversion on 150mm Hot-Wall CVD Reactor T. Höchbauer, C. Heidorn and N. Tsavdaris	123
Germanium Incorporation in Silicon Carbide Epitaxial Layers Using Molecular Beam Epitaxy on 4H-SiC Substrates J. Pezoldt, C. Zgheib, T. Stauden, G. Ecke, T. Kups, H.O. Jacobs and P. Weih	127
A Study of CVD Growth Parameters to Fill 50-μm-Deep 4H-SiC Trenches S. Ji, R. Kosugi, K. Kojima, K. Adachi, Y. Kawada, K. Mochizuki, A. Nagata, Y. Matsukawa, Y. Yonezawa, S. Yoshida and H. Okumura	131
Effect of HCL on Surface Free Energy of SiC during CVD Trench Filling K. Mochizuki, S. Ji, R. Kosugi, Y. Yonezawa and H. Okumura	136
High Temperature SiC Reactor Cleaning Using Chlorine Trifluoride Gas Achieved by Purified Pyrolytic Carbon Coating Film K. Kurashima, K. Shioda, H. Habuka, H. Ito, S. Mitani and Y. Takahashi	141

1.4: 3C-SiC and Related Materials

Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates P. Schuh, U. Künecke, G. Litrico, M. Mauceri, F. La Via, S. Monnoye, M. Zielinski and P.J. Wellmann	149
Novel Carbon Treatment to Create an Oriented 3C-SiC Seed on Silicon M. Zielinski, S. Monnoye, H. Mank, F. Torregrosa, G. Grosset and Y. Spiegel	153
Modeling of the PVT Growth Process of Bulk 3C-SiC - Growth Process Development and Challenge of the Right Materials Data Base M. Schöler, P. Schuh, J. Steiner and P.J. Wellmann	157
Structural Strain in Single Layer Graphene Fabricated on SiC W.C. Yu, X.F. Chen, X.B. Hu, X.G. Xu, P. Jin, P. Yu and R.Q. Wang	161

Chapter 2: Characterisation

2.1: Characterisation of the SiC-Oxide Interface

Evaluation of the Impact of Al Atoms on SiO₂/ SiC Interface Property by Using 4H-SiC n⁺-Channel Junctionless MOSFET	
H. Takeda, T. Hosoi, T. Shimura and H. Watanabe	171
Cryogenic Characterization of NH₃ Post Oxidation Annealed 4H-SiC Trench MOSFETs	
J. Berens, G. Pobegen, T. Aichinger, G. Rescher and T. Grasser	175
Surface Morphology of 4H-SiC after Thermal Oxidation	
J. Woerle, V. Šimonka, E. Müller, A. Hössinger, H. Sigg, S. Selberherr, J. Weinbub, M. Camarda and U. Grossner	180
Subthreshold Drain Current Hysteresis of Planar SiC MOSFETs	
B. Asllani, A. Castellazzi, D. Planson and H. Morel	184
Accurate Dopant and Interface Characterization in Oxidized SiC with Refined Non-Contact C-V Technique	
A. Savtchouk, M. Wilson, C. Almeida, D. Marinskiy, R. Hillard and J. Lagowski	189
First Principles Study of the Influence of the Local Steric Environment on the Incorporation and Migration of NO in a-SiO₂	
M.V. Mistry, J. Cottom, K. Patel, A.M. El-Sayed, G. Pobegen, T. Aichinger and A.L. Shluger	194
Evidence for an Abrupt Transition between SiO₂ and SiC from EELS and <i>Ab Initio</i> Modelling	
J. Cottom, M.V. Mistry, G. Gruber, G. Pobegen, T. Aichinger and A.L. Shluger	199
Theory of Carbon-Vacancy Diffusion at the SiO₂/4H-SiC Interface	
H. Alsnani, J.P. Goss, P.R. Briddon, M.J. Rayson and A.B. Horsfall	204
DFT Calculation for Oxidation Reaction of SiC(0001)	
T. Ono	208
Characterization of SiO₂/SiC Near-Interface Oxide Traps with Constant-Capacitance Deep-Level Transient Spectroscopy	
H. Okada	213
Characterization of Near-Interface Traps at Dielectric/SiC Interfaces Using CCDLTS	
I. Jayawardhena, A. Jayawardena, C.K. Jiao, D. Morissette and S. Dhar	217
Atomic Coordination Analysis of Nitrogen Introduced in SiO₂/ SiC Interface and SiO₂ Layer by XAFS Measurement	
M. Kunisu, S. Ogawa, J. Sameshima and M. Yoshikawa	222
Sub-nm-Scale Depth Profiling of Nitrogen in NO- and N₂-Annealed SiO₂/4H-SiC(0001) Structures	
K. Moges, M. Sometani, T. Hosoi, T. Shimura, S. Harada and H. Watanabe	226
SiO₂/SiC MOSFETs Interface Traps Probed by Nanoscale Analyses and Transient Current and Capacitance Measurements	
P. Fiorenza, F. Giannazzo, M. Saggio and F. Roccaforte	230
A Temperature Independent Effect of Near-Interface Traps in 4H-SiC MOS Capacitors	
P. Pande, S. Dimitrijević, D. Haasmann, H.A. Moghadam, P. Tanner and J.S. Han	236
Identification of Near-Interface Trap Distribution by Parameter Estimation	
Y. Yamashita	240
Impact of Pit Defects on the Initial Electrical Characteristics of Planar-MOSFET Devices	
L. Guo, K. Kamei, K. Momose and H. Osawa	244

2.2: Extended and Surface Defects

Observation of Dislocation Conversion in 4H-SiC Epitaxial Wafer by Mirror Projection Electron Microscopy	
T. Isshiki, T. Sato, M. Hasegawa, K. Ohira, K. Kobayashi, A. Miyaki and K. Onuki	251

Monitoring of Substrate and Epilayer Surfaces by Mirror Projection Electron Microscope I. Kamata, K. Ohira, K. Kobayashi, M. Hasegawa, M. Miyata, N. Noguchi, S. Takami and H. Tsuchida	255
Optical Discrimination of TSDs and TEDs in 4H-SiC Substrates and Epitaxial Layers by Phase Contrast Microscopy Method R. Hattori, O. Oku, R. Sugie, K. Murakami and M. Kuzuhara	259
Dynamics Analysis of Single Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diode Based on Free Energy A. Kano, A. Goryu, M. Kato, C. Ota, A. Okada, J. Nishio and K. Hirohata	263
Analysis of Basal Plane Dislocation Dynamics in 4H-SiC Crystals during High Temperature Treatment B. Raghothamachar, Y. Yang, J.Q. Guo and M. Dudley	268
Detecting Basal Plane Dislocations Converted in Highly Doped Epilayers Y. Nishihara, K. Kamei, K. Momose and H. Osawa	272
Dislocations Propagation Study Trough High-Resolution 4H-SiC Substrate Mapping R. Anzalone, N. Piluso, A. Severino, S. Lorenti, G. Arena and S. Coffa	276
Initiation of Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diodes A. Okada, C. Ota, J. Nishio, A. Goryu, R. Iijima, K. Nakayama, T. Kato, Y. Yonezawa and H. Okumura	280
Effect of Defects in Silicon Carbide Epitaxial Layers on Yield and Reliability H. Das, S. Sunkari, J. Justice, H. Pham and K.S. Park	284
Evaluation of Effect of Mechanical Stress on Stacking Fault Expansion in 4H-SiC P-i-N Diode A. Goryu, A. Kano, M. Kato, C. Ota, A. Okada, J. Nishio, S. Izumi and K. Hirohata	288

2.3: Characterisation of SiC Polytypes

Deep Electronic Levels in n-Type and p-Type 3C-SiC M. Schöler, M.W. Lederer and P.J. Wellmann	297
Combined EPR and Photoluminescence Study of Electron and Proton Irradiated 3C-SiC A. Al Atem, V. Bratus, B. Canut, J. Lefevre, G. Guillot and J.M. Bluet	301
Effects of Aluminum Incorporation on the Young's Modulus of 3C-SiC Epilayers J.B. Messaoud, J.F. Michaud, M. Zielinski and D. Alquier	305
Electrically Active Levels Generated by Long Oxidation Times in 4H-SiC L. Knoll, L. Kranz and G. Alfieri	309
Minority Carrier Lifetime Measurements on 4H-SiC Epiwafers by Time-Resolved Photoluminescence and Microwave Detected Photoconductivity J. Beyer, N. Schöler, J. Erlekampf, B. Kallinger, P. Berwian, K. Dornich and J. Heitmann	313
Carrier Transport Mechanisms in Ion Implanted and Highly-Doped p-Type 4H-SiC(Al) A. Parisini and R. Nipoti	318
Relationship between Temperature Dependencies of Resistivity and Hall Coefficient in Heavily Al-Doped 4H-SiC Epilayers H. Matsuura, R. Nishihata, A. Takeshita, T. Imamura, K. Takano, K. Okuda, A. Hidaka, S. Ji, K. Eto, K. Kojima, T. Kato, S. Yoshida and H. Okumura	324
4H-SiC p-Type Doping Determination from Secondary Electrons Imaging M. Kayambaki, N. Makris, K. Tsagaraki, H. Peyré, A. Stavrinidis, G. Konstantinidis and K. Zekentes	328
Ultra-Fast and High-Precision Crystal Orientation Measurements on 4H-SiC N. Schöler, T. Weißbach, H.A. Bradaczek, H. Berger and K. Dornich	332
Study of Nitrogen Doping Effect on Lattice Strain Variation in 4H-SiC Substrates by Synchrotron X-Ray Contour Mapping Method T. Ailihumaer, Y. Yang, J.Q. Guo, B. Raghothamachar and M. Dudley	336
Newly Resolved Phonon-Assisted Transitions and Fine Structure in the Low Temperature Wavelength Modulated Absorption and Photoluminescence Spectra of 6H SiC W.M. Klahold, W.J. Choyke and R.P. Devaty	341
High Resolution Investigation of Stacking Fault Density by HRXRD and STEM E.G. Barbagioanni, A. Alberti, C. Bongiorno, E. Smecca, M. Zimbone, R. Anzalone, G. Litrico, M. Mauceri, A. La Magna and F. La Via	346

2.4: New SiC Material Functionality

Electrical Characterisation of Thick 3C-SiC Layers Grown on Off-Axis 4H-SiC Substrates F. Li, V. Jokubavicius, M.R. Jennings, R. Yakimova, A. Pérez Tomás, S. Russell, Y. Sharma, F. Roccaforte, P.A. Mawby and F. La Via	353
Nano and Micro-Scale Simulations of Si/4H-SiC and Si/3C-SiC NN-Heterojunction Diodes M.H. Rashid, A. Koel and T. Rang	357
Characterization of β-Silicon Carbide and Potential Use as Irradiation Temperature Monitor J. Vande Pitte, C. Detavernier, J. Lauwaert, I. Uytdenhouten, A. Gusarov and J. Wagemans	362
Terahertz Emission from SiC Natural Superlattices in Strong Electrical Field V.I. Sankin, A.G. Petrov, S. Nagalyuk, P.P. Shkrebiy, E.V. Kalinina and A.A. Lebedev	367

Chapter 3: Processing

3.1: Ion Implantation

Recent Advances in the Doping of 4H-SiC by Channeled Ion Implantation A. Hallén, M.K. Linnarsson and L. Vines	375
Channeled Implantations of p-Type Dopants into 4H-SiC at Different Temperatures M.K. Linnarsson, A. Hallén, L. Vines and B.G. Svensson	382
Channeling in 4H-SiC from an Application Point of View P. Pichler, T. Sledziewski, V. Häublein, A.J. Bauer and T. Erlbacher	386
Fabrication and Characterization of 3.3-kV SiC DMOSFET with Self-Aligned Channels Formed by Tilted Ion Implantation T. Morikawa, S. Sato and A. Shima	390
Comparison of Ranges for Al Implantations into 4H-SiC (0001) Using Channeled Ions and an Ion Energy in the Bethe-Bloch Region K. Mochizuki, R. Kosugi, Y. Yonezawa and H. Okumura	394
Thermal Annealing of High Dose P Implantation in 4H-SiC C. Calabretta, M. Zimbone, E.G. Barbagiovanni, S. BONINELLI, N. Piluso, A. Severino, M.A. di Stefano, S. Lorenti, L. Calcagno and F. La Via	399
High-Concentration, Low-Temperature, and Low-Cost Excimer Laser Doping for 4H-SiC Power Device Fabrication K. Imokawa, T. Kikuchi, K. Okamoto, D. Nakamura, A. Ikeda, T. Asano and H. Ikenoue	403
Effects of Thermal Annealing Processes in Phosphorous Implanted 4H-SiC Layers A. Severino, D. Mello, S. BONINELLI, F. Roccaforte, F. Giannazzo, P. Fiorenza, C. Calabretta, L. Calcagno, N. Piluso and G. Arena	407
Increasing Laser-Doping Depth of Al in 4H-SiC by Using Expanded-Pulse Excimer Laser A. Ikeda, T. Shimokawa, H. Ikenoue and T. Asano	412
Activation Energy for the Post Implantation Annealing of 10^{19} cm^{-3} and 10^{20} cm^{-3} Ion Implanted Al in 4H SiC R. Nipoti, M.C. Canino, S. Sapienza, M. Bellettato, G. Sozzi and G. Alfieri	416
1300°C Annealing of $1 \times 10^{20} \text{ Al}^+$ Ion Implanted 3C-SiC R. Nipoti, M.C. Canino, F. Bonafe, F. Torregrosa, S. Monnoye, H. Mank and M. Zielinski	420
Raman Spectroscopy Characterization of Ion Implanted 4H-SiC Z.W. Xu, Y. Song, M. Rommel, T. Liu, M. Kocher, Z.D. He, H. Wang, B.T. Yao, L. Liu and F.Z. Fang	424
Surface Characterization of Ion Implanted 4H-SiC Epitaxial Layers with Ion Energy and Concentration Variations H.K. Kim, S.J. Kim, J. Buettner, M.W. Lim, T. Erlbacher, A.J. Bauer, S.M. Koo, N.S. Lee and H.K. Shin	429

On the Origin of Charge Compensation in Aluminum-Implanted n-Type 4H-SiC by Analysis of Hall Effect Measurements	
J. Weisse, M. Hauck, T. Sledziewski, M. Krieger, A.J. Bauer, H. Mitlehner, L. Frey and T. Erlbacher	433
Lateral Straggling of Ion Implantation Distributions in 4H-SiC Investigated by SIMS	
J. Mütting, V. Bobal, A. Azarov, B.G. Svensson and U. Grossner	437
Decoration of Al Implantation Profiles in 4H-SiC by Bevel Grinding and Dry Oxidation	
M. Kocher, T. Erlbacher, M. Rommel and A.J. Bauer	441
Determination of Compensation Ratios of Al-Implanted 4H-SiC by TCAD Modelling of TLM Measurements	
M. Kocher, B.T. Yao, J. Weisse, M. Rommel, Z.W. Xu, T. Erlbacher and A.J. Bauer	445

3.2: SiC-Oxide Interface Processing

Characterization of Ba-Introduced Thin Gate Oxide on 4H-SiC	
K. Muraoka, S. Ishikawa, H. Sezaki, T. Maeda and S. Kuroki	451
Study of the Post-Oxidation-Annealing (POA) Process on Deposited High-Temperature Oxide (HTO) Layers as Gate Dielectric in SiC MOSFET	
A. Severino, N. Piluso, M.A. di Stefano, F. Cordiano, M. Camalleri and G. Arena	456
Electrical Characterization of MOCVD Grown Single Crystalline AlN Thin Films on 4H-SiC	
R.Y. Khosa, J.T. Chen, K. Pálsson, R. Karhu, J. Hassan, N. Rorsman and E.Ö. Sveinbjörnsson	460
Improved SiO₂/ 4H-SiC Interface Defect Density Using Forming Gas Annealing	
S. Wirths, G. Alfieri, A. Prasmusinto, A. Mihaila, L. Kranz, M. Bellini and L. Knoll	465
Improved Field Effect Mobility in Si-Face 4H-SiC MOSFETs with a Deposited SiN_x Interface Layer	
T. Kumazawa, M. Okamoto, M. Iijima, Y. Iwahashi, S. Fujikake, T. Araoka, T. Tawara, H. Kimura, K. Hamada, S. Harada and H. Okumura	469
Evidence of Channel Mobility Anisotropy on 4H-SiC MOSFETs with Low Interface Trap Density	
M. Cabello, V. Soler, D. Haasmann, J. Montserrat, J. Rebollo and P. Godignon	473
Electrical Properties of Thermal Oxide on 3C-SiC Layers Grown on Silicon	
P. Fiorenza, G. Greco, S. Di Franco, F. Giannazzo, S. Monnoye, M. Zielinski, F. La Via and F. Roccaforte	479

3.3: Contacts and Other Processing

Fabrication and Characterization of Ohmic Contacts to 3C-SiC Layers Grown on Silicon	
M. Spera, G. Greco, R. Lo Nigro, S. Di Franco, D. Corso, P. Fiorenza, F. Giannazzo, M. Zielinski, F. La Via and F. Roccaforte	485
Comparison between Ni-SALICIDE and Self-Aligned Lift-Off Used in Fabrication of Ohmic Contacts for SiC Power MOSFET	
T. Sledziewski, T. Erlbacher, A.J. Bauer, L. Frey, X.M. Chen, Y.L. Zhao, C. Li and X.P. Dai	490
Microstructural Analysis of Ti/Ni Bilayer Ohmic Contacts on 4H-SiC Layers	
V. Sundaramoorthy, L. Kranz and G. Alfieri	494
Optimization of Ni/Nb Ratio for High-Temperature-Reliable Ni/Nb Silicide Ohmic Contact on 4H-SiC	
V.V. Cuong, S. Ishikawa, H. Sezaki, T. Maeda, S. Yasuno, T. Koganezawa and S. Kuroki	498
Laser Annealing Simulations of Metallisations Deposited on 4H-SiC	
C. Berger, J.F. Michaud, D. Chouteau and D. Alquier	502
Argon Bombardment of 4H Silicon Carbide Substrates for Tailored Schottky Diode Barrier Heights	
M. Schneider, L. Stöber, J.P. Konrath, F. Patocka and U. Schmid	506
Surface Effects of Passivation within Mo/4H-SiC Schottky Diodes through MOS Analysis	
A.B. Renz, V.A. Shah, O.J. Vavasour, Y. Bonyadi, G.W.C. Baker, F. Li, T.X. Dai, M. Walker, P.A. Mawby and P.M. Gammon	511

Deep Level Transient Spectroscopy (DLTS) Study of 4H-SiC Schottky Diodes and PiN Diodes	
X. Zhou, G. Pandey, R. Ghandi, P.A. Losee, A. Bolotnikov and T.P. Chow	516
Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher	
K. Kurashima, R. Kawasaki, K. Irikura, S. Okuyama, H. Habuka, Y. Takahashi and T. Kato	520
High-Efficiency Planarization of SiC Wafers by Water-CARE (Catalyst-Referred Etching) Employing Photoelectrochemical Oxidation	
H. Kida, D. Toh, P.V. Bui, A. Isohashi, R. Ohnishi, S. Matsuyama, K. Yamauchi and Y. Sano	525
Impact of Subsurface Damage on SiC Wafer Shape	
K. Moeggenborg, I. Manning, J. Searson and G.Y. Chung	530

Chapter 4: Devices and Applications

4.1: Rectifying Devices

Study of 4H-SiC Superjunction Schottky Rectifiers with Implanted P-Pillars	
G.W.C. Baker, C.W. Chan, T.X. Dai, A.B. Renz, F. Li, V.A. Shah, P.A. Mawby and P.M. Gammon	539
Surge Current and Avalanche Robustness of Commercial 1200 V SiC Schottky Diodes	
S.G. Sundaresan, V. Mulpuri and R. Singh	544
Influence of Trench Design on the Electrical Properties of 650V 4H-SiC JBS Diodes	
O. Rusch, J. Moulton and T. Erlbacher	549
The Impact of Non-Ideal Ohmic Contacts on the Performance of High-Voltage SiC MPS Diodes	
Y. Huang, J. Buettner, B. Lechner and G. Wachutka	553
On the Development of 1700V SiC JBS Diodes in a 6-Inch Foundry	
N. Yun, E. Liu, W.J. Sung, A.S. Larrea, D. Franca, T. Gorczyca, A. Bialy, W.L. Collison, J. Prudhomme, P.Y. Hung, S. Valente, S. Dunn, B. Sapp and J. Hedrick	558
Mechanisms and Characteristics of Large-Area High-Current-Density 4H-SiC Trench Junction Barrier Schottky Diodes	
Y.D. Tang, S.X. Dong, Y. Bai, C.Y. Yang, C. Li and X.Y. Liu	562
Advanced Electrical Characterisation of High Voltage 4H-SiC PiN Diodes	
B. Asllani, D. Planson, P. Bevilacqua, J.B. Fonder, B. Choucoute, H. Morel and L.V. Phung	567
Performance of 4H-SiC Bipolar Diodes as Temperature Sensor at Low Temperatures	
L. di Benedetto, C.D. Matthus, T. Erlbacher, A.J. Bauer, G.D. Licciardo, A. Rubino and L. Frey	572
Multi-Barrier Height Characterization and DLTS Study on Ti/W 4H-SiC Schottky Diode	
T. Zhang, C. Raynaud and D. Planson	576

4.2: Power MOSFET

Comparison of SiC MOSFET Characteristics Following Body-Diode Forward-Current Stress	
R. Green, A. Lelis and F.L. Nouketcha	583
Achieving Reduced Specific On-Resistance in 1.2 kV SiC Power MOSFETs at Elevated Temperature	
K.J. Han and B.J. Baliga	588
Temperature Dependency of Silicon Carbide MOSFET On-Resistance Characterization and Modeling	
D.L. Dang, M. Urbain and S. Rael	592
Temperature Dependence of dV/dt Impact on the SiC-MOSFET	
S. Nakata and S. Tanaka	596
1.2 kV SiC Trench-Gate MOSFETs with Dual Shielding Regions	
A. Agarwal, K.J. Han and B.J. Baliga	600
Design Optimization of 1.2kV 4H-SiC Trench MOSFET	
T.X. Dai, P.M. Gammon, V.A. Shah, X. Deng, M.R. Jennings and P.A. Mawby	605

Inverse Modeling of 4H-SiC Trench Gate MOSFETs Validated with Electrical and Physical Characterization	
A. Sakai, K. Eikyu, K. Hisada, Y. Yamashita, K. Arai, H. Arie, Y. Akiyama and T. Yamashita	609
Suppression of Short-Channel Effects in 4H-SiC Trench MOSFETs	
T. Ishii, S. Kuroki, H. Sezaki, S. Ishikawa, T. Maeda, T. Makino, T. Ohshima, M. Östling and C. Zetterling	613
1.2-kV SiC Trench-Etched Double-Diffused MOS (TED-MOS)	
T. Suto, N. Watanabe, Y. Bu, H. Miki, N. Tega, Y. Mori, D. Hisamoto and A. Shima	617
An Investigation into the Dynamic Behavior of 3.3kV MOSFETs Body Diode	
A. Mihaila, E. Bianda, L. Knoll, P. Godignon, V. Soler, L. Kranz, G. Alfieri, U. Badstübner, F. Canales and M. Rahimo	621
Experimental Study of High-Temperature Switching Performance of 1.2kV SiC JBSFET in Comparison with 1.2kV SiC MOSFET	
A. Kanale, B.J. Baliga, K.J. Han and S. Bhattacharya	625
Design of a 4H-SiC RESURF n-LDMOS Transistor for High Voltage Integrated Circuits	
J. Weisse, H. Mitlehner, L. Frey and T. Erlbacher	629
Impact of Interface Trap Density of SiC-MOSFET in High-Temperature Environment	
S. Sato, M. Masunaga, Y. Mori, N. Sugii and A. Shima	633

4.3: Bipolar, JFETs and Other Switching Devices

Performance Improvement of >10kV SiC IGBTs with Retrograde p-Well	
A. Tiwari, M. Antoniou, N. Lophitis, S. Perkins, T. Trajkovic and F. Udrea	639
Deep Trench Termination Structure with p-Type SiC Layer for Improved Reliability of High Voltage IGBT	
W.F. Du, Y.H. Wang, R. Jin, K. Pu, W.H. Zhang, J. Zeng, M.N. Darwish, J. Liu and T. Zhu	643
Improved Device Characteristics Obtained Using a Novel High-K Dielectric Stack for 4H-SiC n-IGBT: HfO₂-SiO₂- AlN	
S. Kotamraju and P. Vudumula	647
15 kV n-GTOs in 4H-SiC	
S.H. Ryu, D.J. Lichtenwalner, M. O'Loughlin, C. Capell, J. Richmond, E. Van Brunt, C. Jonas, Y. Lemma, A.A. Burk, B. Hull, M. McCain, S. Sabri, H. O'Brien, A. Ogunniyi, A. Lelis, J. Casady, D. Grider, S. Allen and J.W. Palmour	651
SiC Charge-Balanced Devices Offering Breakthrough Performance Surpassing the 1-D Ron versus BV Limit	
A. Bolotnikov, P.A. Losee, R. Ghandi, S. Kennerly, R. Datta and X. She	655
Improvement of Switching Characteristics in 6.5-kV SiC IGBT with Novel Drift Layer Structure	
N. Watanabe, H. Yoshimoto, Y. Mori and A. Shima	660
Simulation Study for the Structural Cell Design Optimization of 15kV SiC p-Channel IGBTs	
X.L. Tian, B. Tan, Y. Bai, J.L. Hao, C.Y. Yang and X.Y. Liu	666
TCAD Model Calibration of High Voltage 4H-SiC Bipolar Junction Transistors	
D. Johannesson, M. Nawaz and H.P. Nee	670
Silicon Carbide BJT Oscillator Design Using S-Parameters	
M.W. Hussain, H. Elahipanah, S. Rodriguez, B.G. Malm and A. Rusu	674
Effect of Temperature on the Electrical Characteristics of 4H-SiC Planar n/p-Type Junctionless FET: Physics Based Simulation	
P. Vudumula and S. Kotamraju	679
Compact Modeling of SiC and GaN Junction FETs at High Temperature	
N. Makris, K. Zekentes and M. Bucher	683
High-Voltage SiC-JFET Fabrication and Full Characterization	
B. Asllani, P. Bevilacqua, A. Zaoui, G. Grosset, D. Planson and H. Morel	688
Performance Limits of Vertical 4H-SiC and 2H-GaN Superjunction Devices	
X. Zhou, Z.B. Guo and T.P. Chow	693
First Experimental Test on Bipolar Mode Field Effect Transistor Prototype in 4H-SiC: A Proof of Concept	
L. di Benedetto, G.D. Licciardo, A. Huerner, T. Erlbacher, A.J. Bauer and A. Rubino	697

Development of SOI FETs Based on Core-Shell Si/SiC Nanowires for Sensing in Liquid Environments	
R. Bange, E. Bano, L. Rapenne, A. Mantoux, S.E. Sadow and V. Stambouli	701

4.4: Radiation and Quantum Devices

Creation of Color Centers in SiC PN Diodes Using Proton Beam Writing	
Y. Chiba, Y. Yamazaki, T. Makino, S.I. Sato, N. Yamada, T. Satoh, K. Kojima, S.Y. Lee, Y. Hijikata and T. Ohshima	709
First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC	
A. Csöré, B. Magnusson, N.T. Son, A. Gällström, T. Ohshima, I. Ivanov and Á. Gali	714
Radiation Effects on 1.7kV Class 4H-SiC Power Devices: Development of Compact Simulation Models	
P. Hazdra and S. Popelka	718
Electrophysical and Optical Properties of 4H-SiC UV Detectors Irradiated with Electrons	
E.V. Kalinina, A.A. Lebedev, V.V. Kozlovski, V. Zabrodski, A.M. Strel'chuk and I.P. Nikitina	722
Direct Bonding of 4H-SiC and SOI Wafers for Radiation-Hardened Image Sensors	
F. Hasebe, T. Meguro, T. Makino, T. Ohshima, Y. Tanaka and S. Kuroki	726
Dependence of the Carrier Removal Rate in 4H-SiC PN Structures on the Irradiation Temperature	
A.A. Lebedev, K.S. Davydovskaya, V.V. Kozlovski, O. Korolkov, N. Sleptsuk and J. Toompuu	730
Change in the Parameters of Electron-Irradiated 4H-SiC Schottky Diodes as a Function of the Time during Low-Temperature Isothermal Annealing	
O. Korolkov, V.V. Kozlovski, A.A. Lebedev, J. Toompuu, N. Sleptsuk and T. Rang	734
Impact of Device Structure on Neutron-Induced Single-Event Effect in SiC MOSFETs	
H. Kono, T. Ohashi, T. Noda and K. Sano	738

4.5: Device Ruggedness and Reliability

Gate Oxide Reliability of SiC MOSFETs and Capacitors Fabricated on 150mm Wafers	
D.J. Lichtenwalner, S. Sabri, E. Van Brunt, B. Hull, S. Ganguly, D.A. Gajewski, S. Allen and J.W. Palmour	745
Novel Method for Evaluation of Negative Bias Temperature Instability of SiC MOSFETs	
J.O. Gonzalez, O. Alatise and P.A. Mawby	749
1200 V SiC MOSFETs with Stable V_{TH} under High Temperature Gate Bias Stress	
J. Franchi, M. Domeij and K. Lee	753
V_T Drift Measurements in SiC Power MOSFETs	
D.B. Habersat, A. Lelis and R. Green	757
Design Considerations for Robust Manufacturing and High Yield of 1.2 kV 4H-SiC VDMOS Transistors	
H. Schlichting, T. Sledziewski, A.J. Bauer and T. Erlbacher	763
Dynamic Characterization and Robustness Test of High Voltage SiC MOSFETs	
V. Soler, M. Cabello, V. Banu, J. Montserrat, J. Rebollo, P. Godignon, E. Bianda, L. Knoll, L. Kranz and A. Mihaila	768
Avalanche Ruggedness Characterization of 10 kV 4H-SiC MOSFETs	
A. Kumar, S. Parashar, E. Van Brunt, S. Sabri, S. Ganguly, S. Bhattacharya and V. Veliadis	773
Avalanche Robustness of 4600 V SiC DMOSFETs	
S.G. Sundaresan, V. Mulpuri, S. Jeliakov and R. Singh	777
Reliability and Ruggedness of Planar Silicon Carbide MOSFETs	
K. Matocha, I.H. Ji and S. Chowdhury	782
Capability of SiC MOSFETs under Short-Circuit Tests and Development of a Thermal Model by Finite Element Analysis	
D. Cavallaro, M. Pulvirenti, E. Zanetti and M. Saggio	788
Comparative Study on the Repetitive Unclamped-Inductive-Switching Capability(R-UIS) of 1200V 160mOhm SiC Planar Gate MOSFETs	
I.H. Ji, S. Chowdhury, B. Powell, K. Chetty, S. Banerjee and K. Matocha	792

Superior Short Circuit Performance of 1.2kV SiC JBSFETs Compared to 1.2kV SiC MOSFETs	
A. Kanale, K.J. Han, B.J. Baliga and S. Bhattacharya	797
Optimization of 1700V SiC MOSFET for Short Circuit Ruggedness	
A. Bolotnikov, P.A. Losee, R. Ghandi, A. Halverson and L. Stevanovic	801
Industrial and Body Diode Qualification of Gen-III Medium Voltage SiC MOSFETs: Challenges and Solutions	
E. Van Brunt, M. O'Loughlin, A.A. Burk, B. Hull, S.H. Ryu, J. Richmond, Y. Khlebnikov, E. Balkas, D.A. Gajewski, S. Allen and J.W. Palmour	805

4.6: CMOS and Integrated Circuits

Demonstration of 4H-SiC JFET Digital ICs Across 1000°C Temperature Range without Change to Input Voltages	
P.G. Neudeck, D.J. Spry, M.J. Krasowski, N.F. Prokop and L.Y. Chen	813
A Monolithic 500°C D-Flip Flop Realized in Bipolar 4H-SiC TTL Technology	
M. Shakir, S.B. Hou and C. Zetterling	818
A Study on Fastening the Switching Speed for Wide Bandgap Semiconductor Based Super Cascode	
X.G. Wang and M. Yamamoto	823
Improving 5V Digital 4H-SiC CMOS ICs for Operating at 400°C Using PMOS Channel Implantation	
M. Albrecht, T. Erlbacher, A.J. Bauer and L. Frey	827
High Temperature High Current Gain IC Compatible 4H-SiC Phototransistor	
S.B. Hou, P.E. Hellström, C. Zetterling and M. Östling	832
4H-SiC Trench pMOSFETs for High-Frequency CMOS Inverters	
J. Inoue, S. Kuroki, S. Ishikawa, T. Maeda, H. Sezaki, T. Makino, T. Ohshima, M. Östling and C. Zetterling	837
SiC Vertical-Channel n- and p-JFETs Fully Fabricated by Ion Implantation	
M. Kaneko, U. Grossner and T. Kimoto	841
Improved Offset Voltage Stability of 4H-SiC CMOS Operational Amplifier by Increasing Gamma Irradiation Resistance	
M. Masunaga, S. Sato, R. Kuwana, I. Hara and A. Shima	845

4.7: Modules and Converters

Comparative Study of Developed 1200V/50A Full SiC IEMOS and VMOS Power Module	
K. Hayashi, T. Funaki, H. Michikoshi and K. Fukuda	851
An Efficient Simulation Methodology to Quantify the Impact of Parameter Fluctuations on the Electrothermal Behavior of Multichip SiC Power Modules	
A. Borghese, A.P. Catalano, M. Riccio, L. Codecasa, A. Fayyaz, V. d'Alessandro, A. Castellazzi, L. Maresca, G. Breglio and A. Irace	855
6.5 kV Si/SiC Hybrid Power Module Technology	
Y. Sharma, P. Mumby-Croft, L. Ngwendson, M. Packwood, L. Coulbeck, M. Birkett, C. Kong, H. Jiang, Y. Wang and I. Deviny	859
Development of a High-Speed Switching Silicon Carbide Power Module	
S. Sato, F. Kato, H. Tanisawa, K. Kouji, K. Watanabe, Y. Murakami, Y. Kobayashi, H. Sato, H. Yamaguchi and S. Harada	864
SiC Power Devices for Applications in Hybrid and Electric Vehicles	
N. Zabihi, A. Mumtaz, T. Logan, T. Daranagama and R.A. McMahon	869
Power Loss Comparison in a BOOST PFC Circuit Considering the Reverse Recovery of the Forward Diode	
W.H. Shao, X.L. Li, H.P. Jiang, X. Guo, Z. Zeng, L. Ran and P.A. Mawby	873